

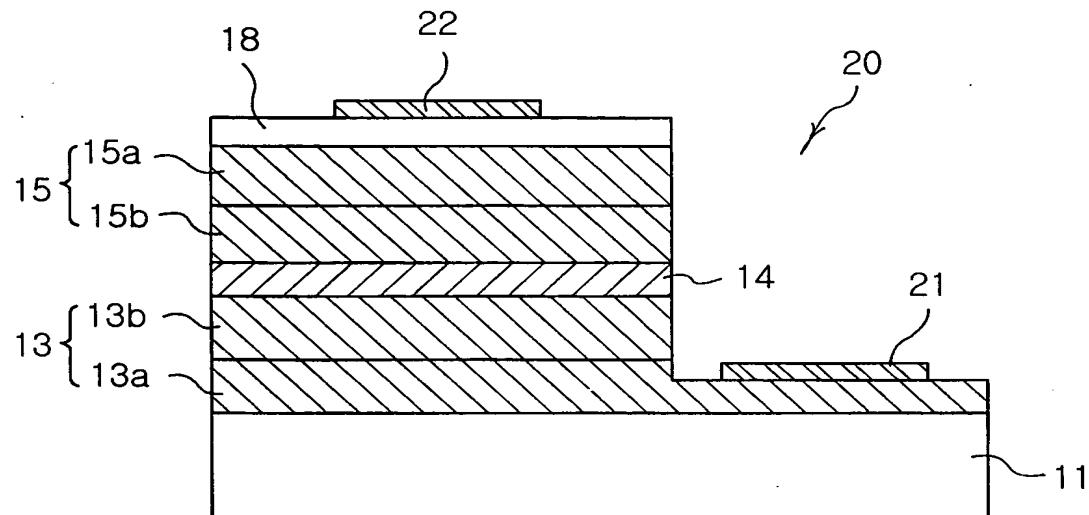
GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE AND

METHOD FOR MANUFACTURING THE SAME

Inventor: Seung Wan CHAE

Docket No. 2336-257

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PRIOR ART

FIG. 1

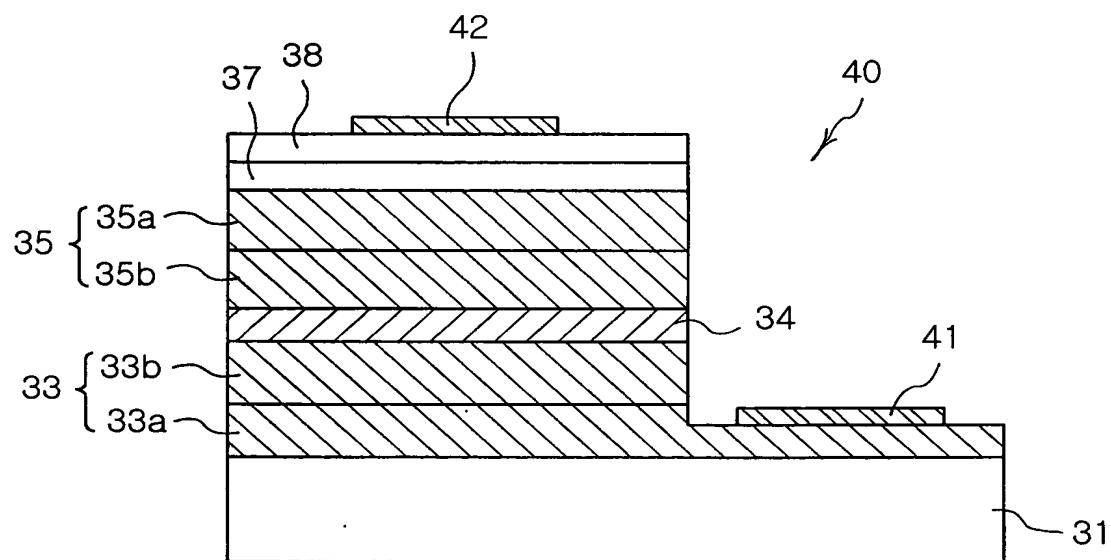


FIG. 2

GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE AND

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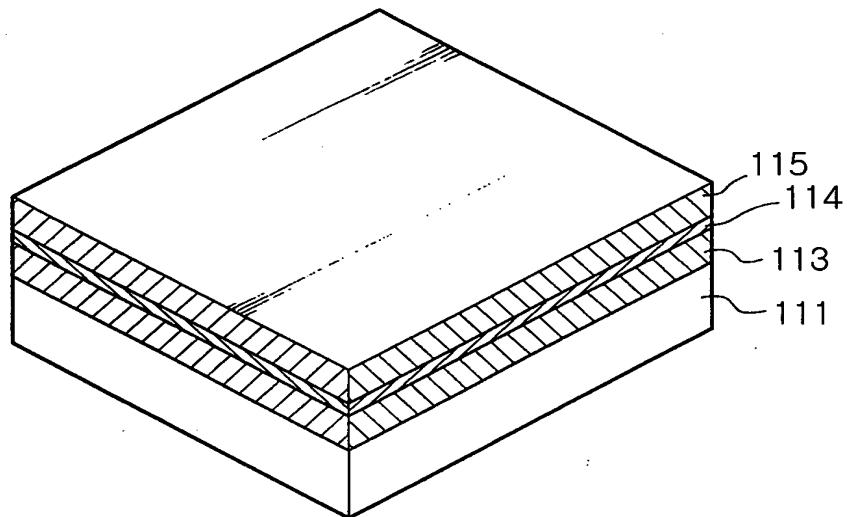


FIG. 3a

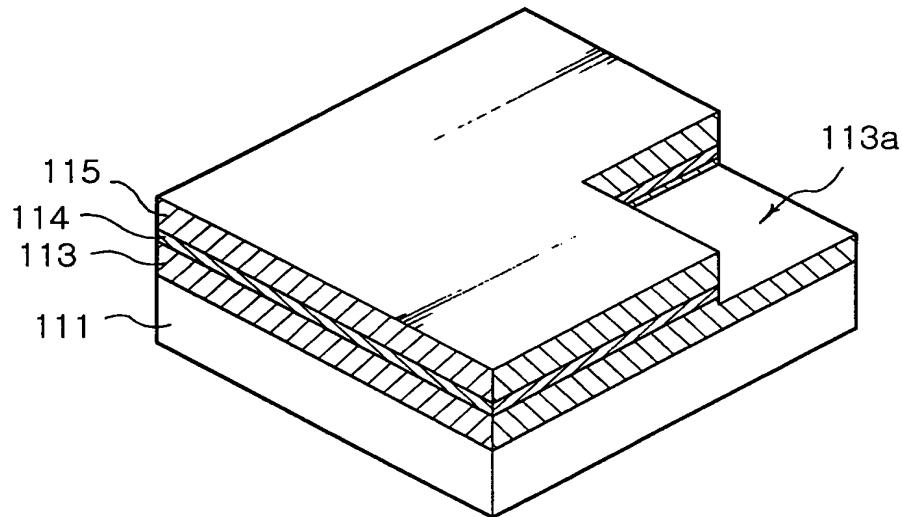


FIG. 3b

GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE AND
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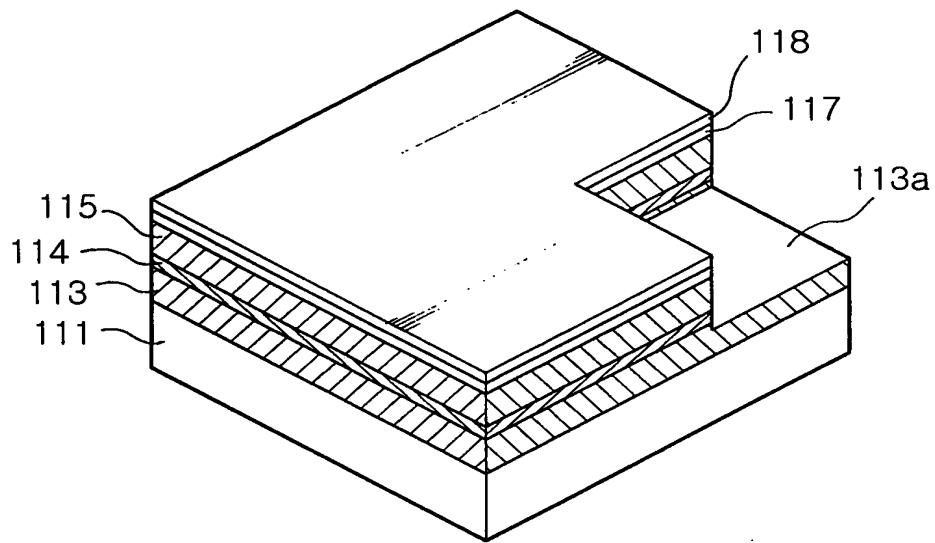


FIG. 3c

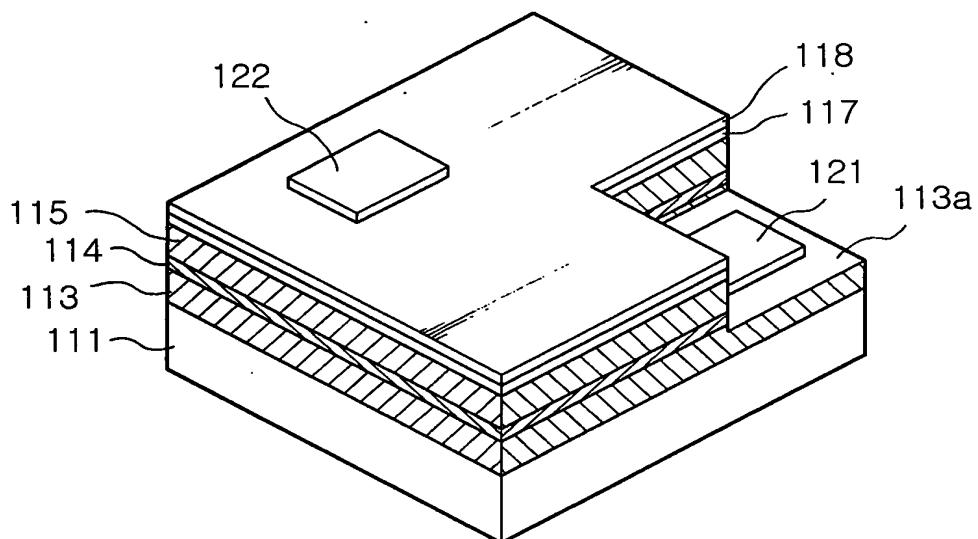


FIG. 3d

GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE AND
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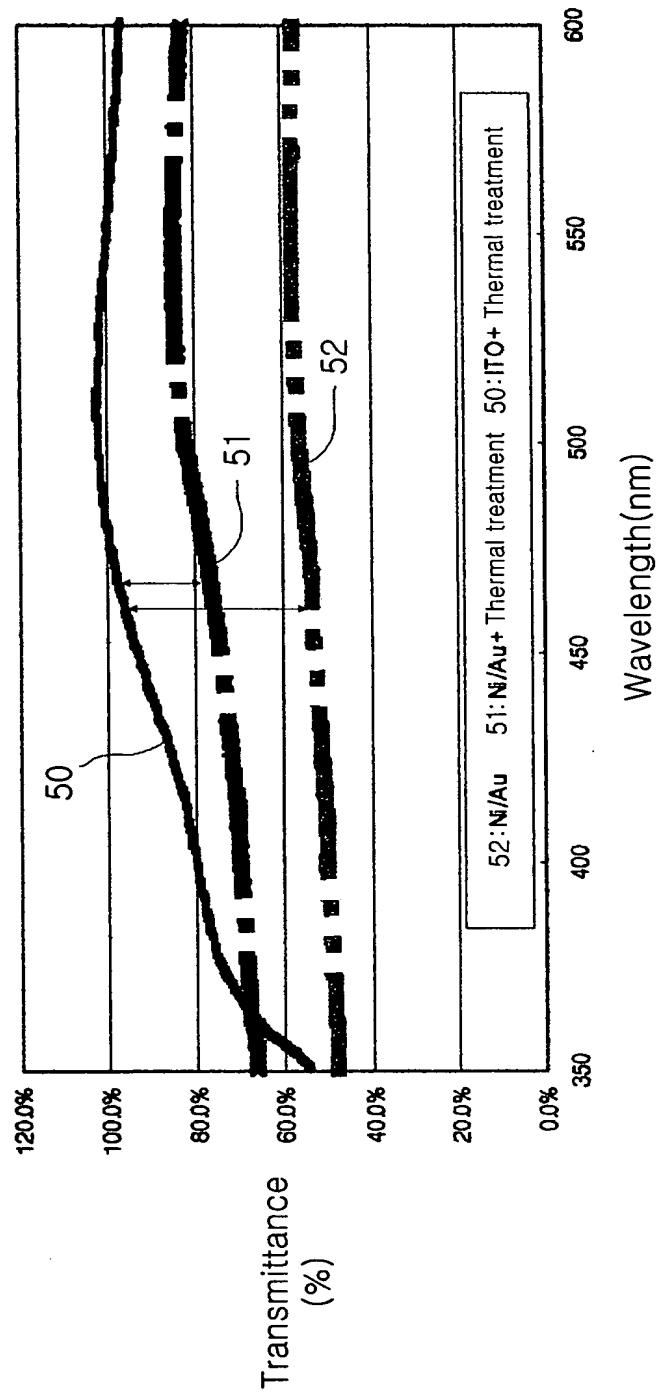


FIG. 4

GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE AND
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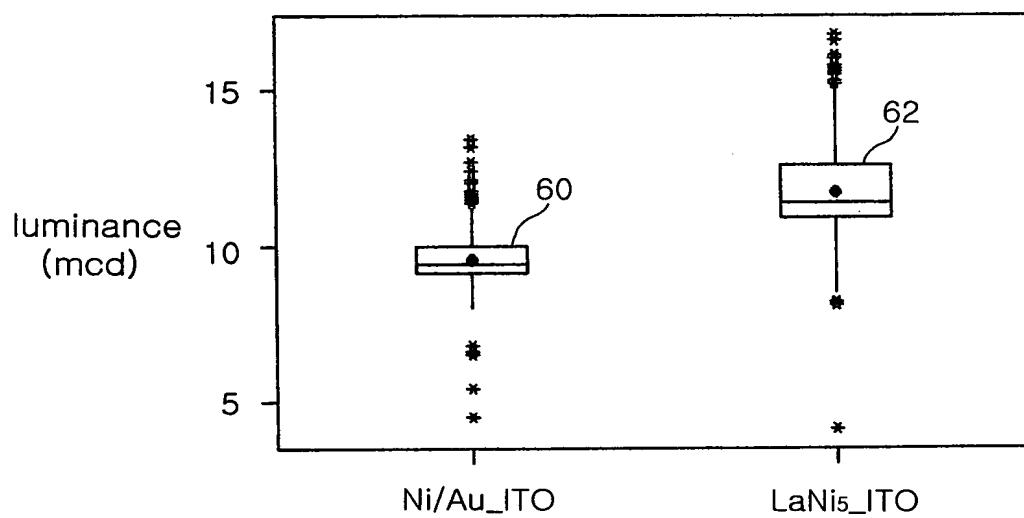


FIG. 5